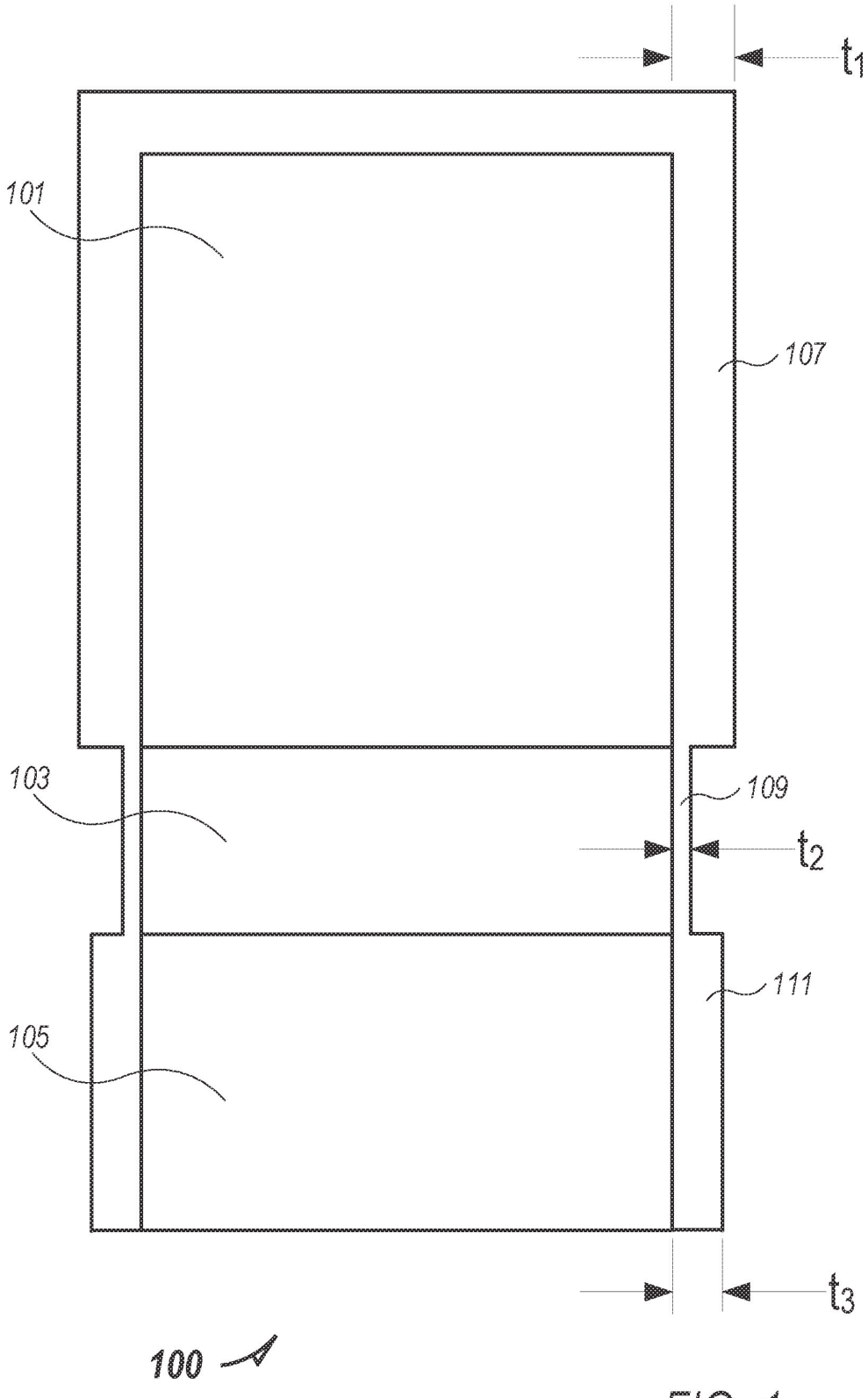


FIG. 1
(PRIOR ART)

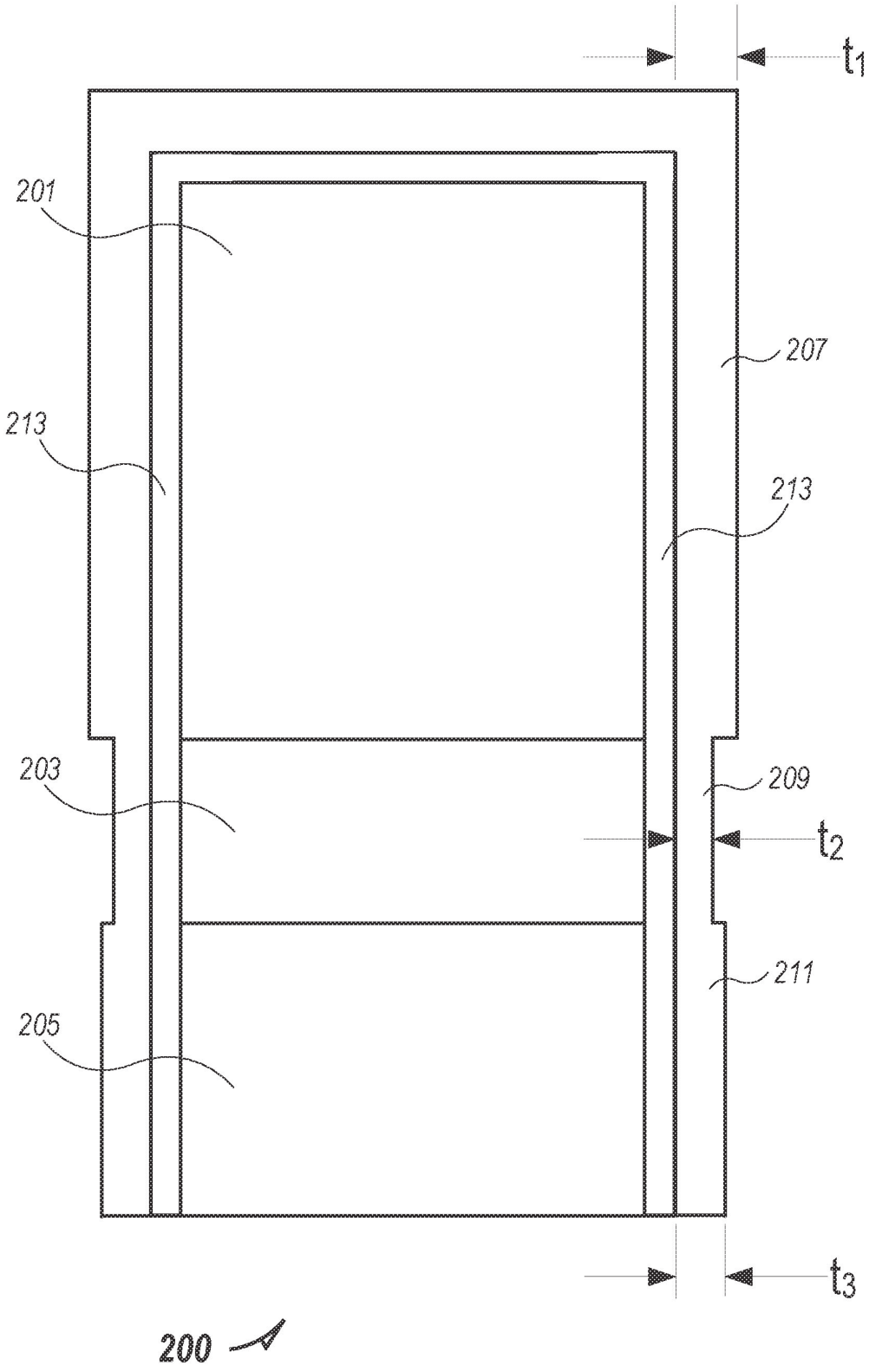


FIG. 2
(PRIOR ART)

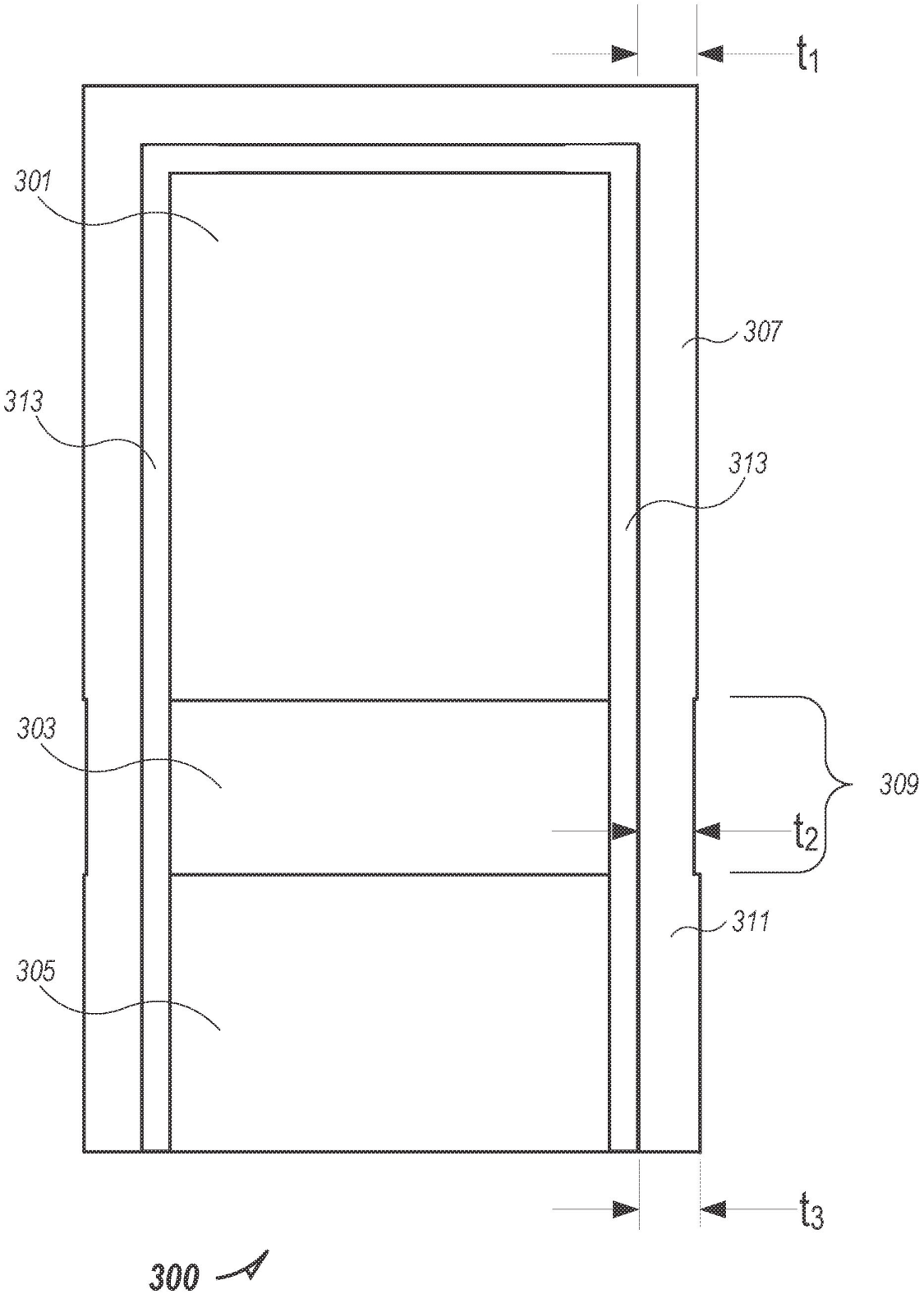


FIG. 3

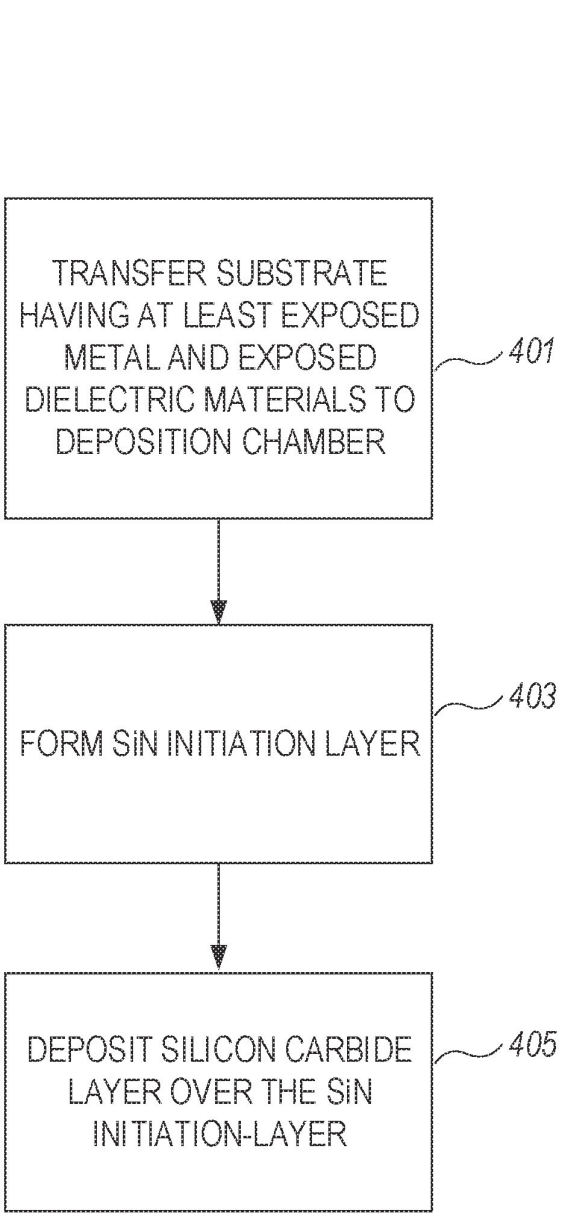

400
TRANSFER SUBSTRATE HAVING AT LEAST EXPOSED METAL AND EXPOSED DIELECTRIC MATERIALS TO DEPOSITION CHAMBER
401
FORM SiN INITIATION LAYER
403
DEPOSIT SILICON CARBIDE LAYER OVER THE SiN INITIATION-LAYER
405

FIG. 4

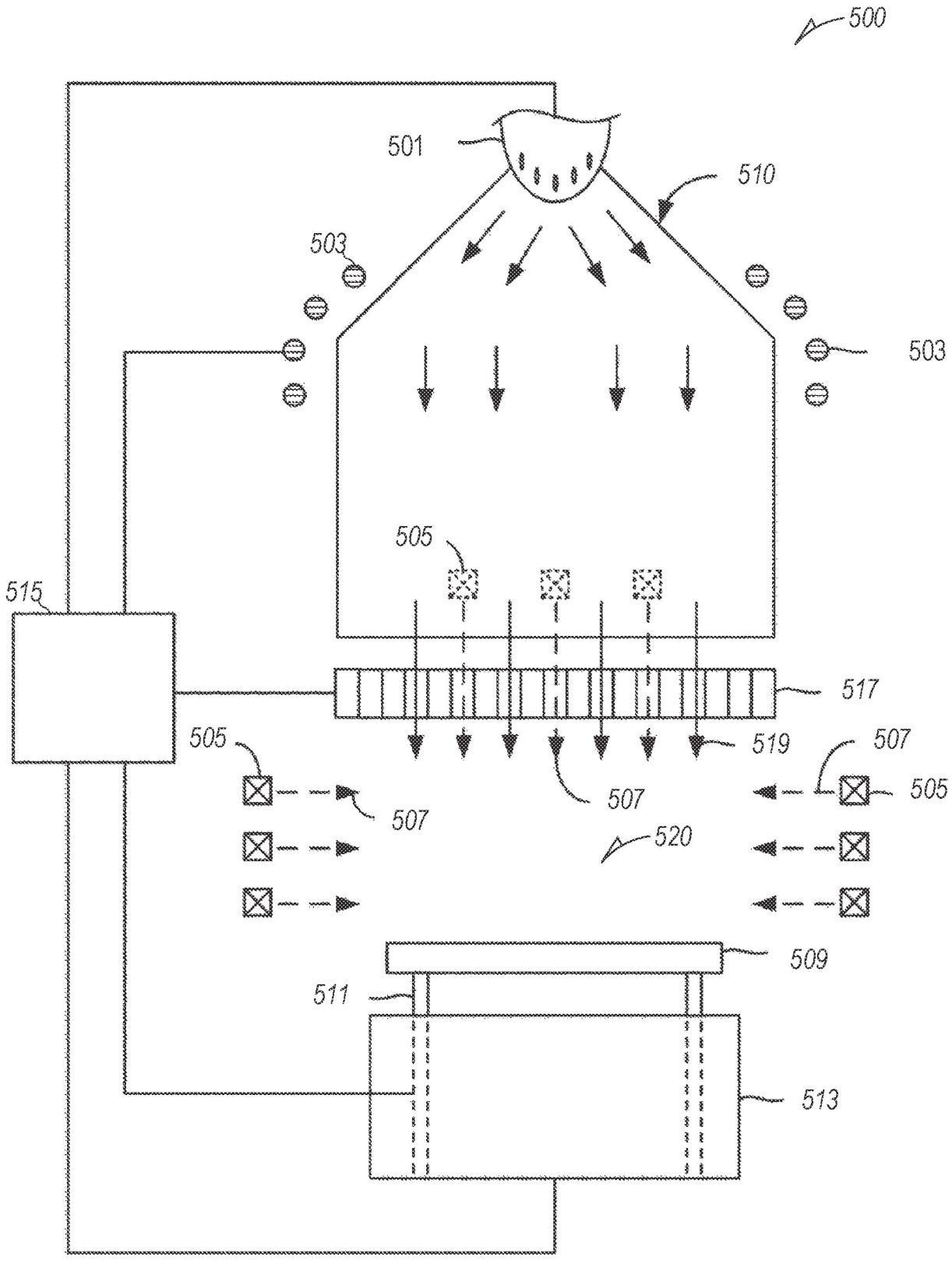

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FIG. 5

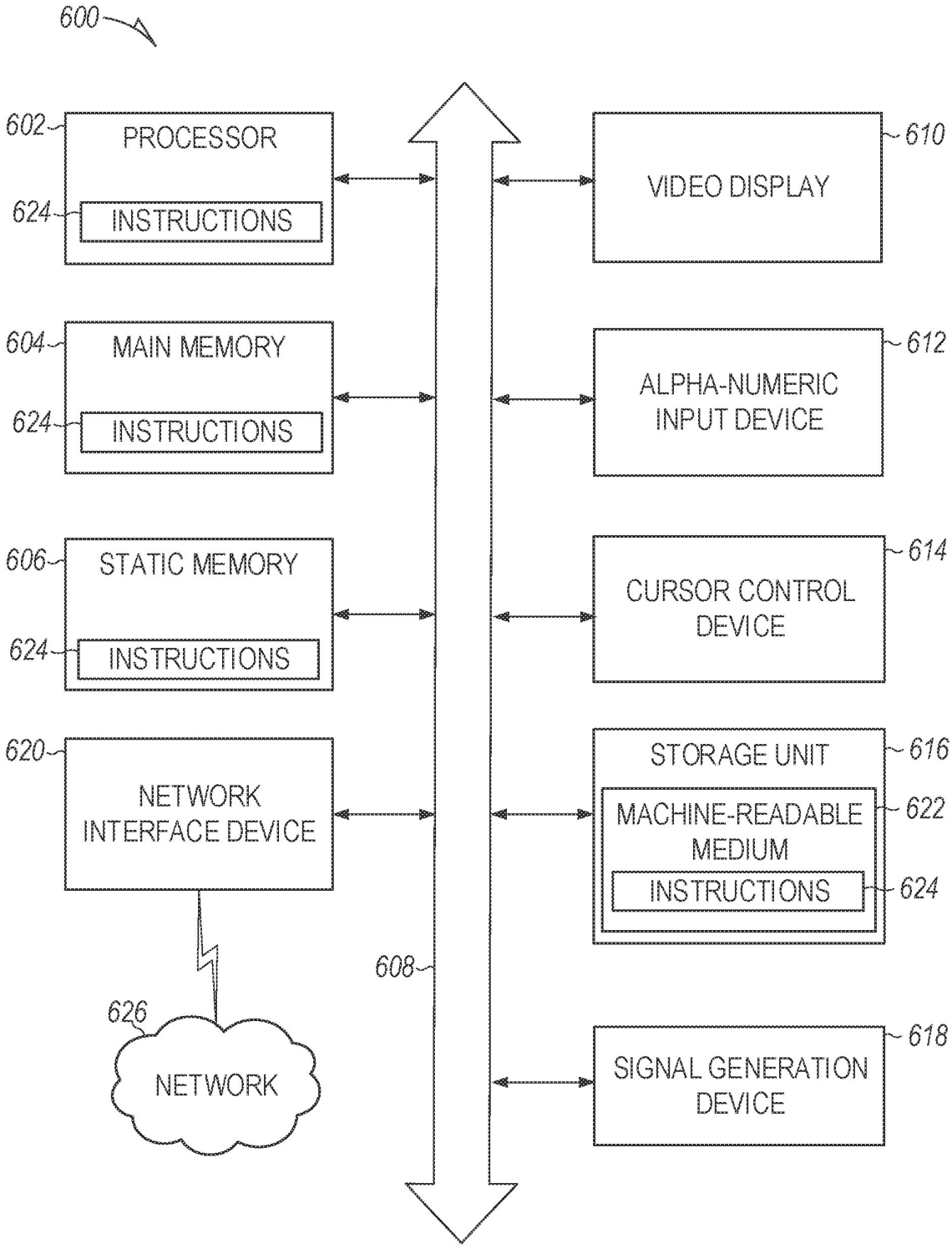

600
602
PROCESSOR
624
INSTRUCTIONS
604
MAIN MEMORY
624
INSTRUCTIONS
606
STATIC MEMORY
624
INSTRUCTIONS
620
NETWORK INTERFACE DEVICE
626
NETWORK
608
610
VIDEO DISPLAY
612
ALPHA-NUMERIC INPUT DEVICE
614
CURSOR CONTROL DEVICE
616
STORAGE UNIT
622
MACHINE-READABLE MEDIUM
624
INSTRUCTIONS
618
SIGNAL GENERATION DEVICE

FIG. 6